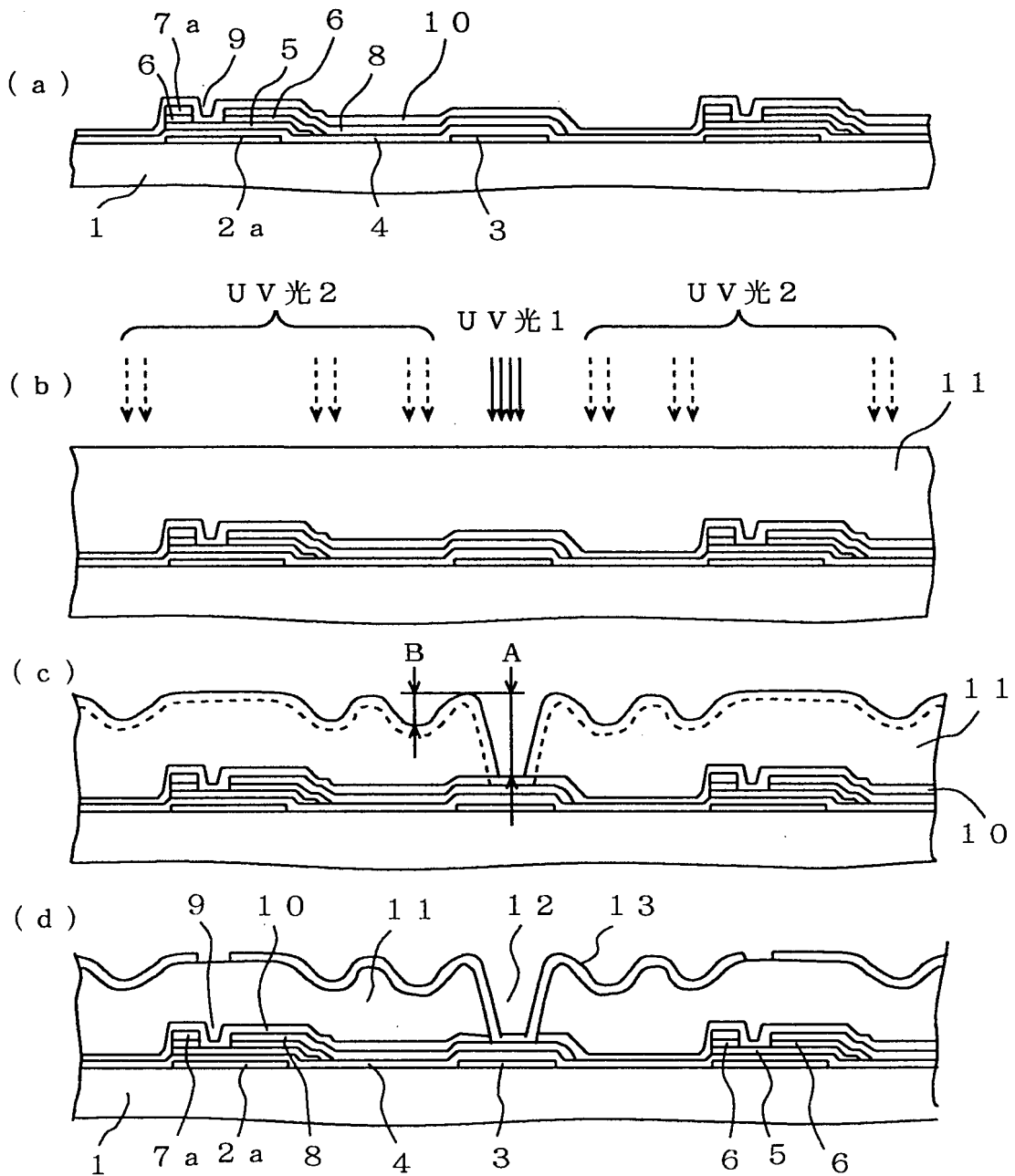


Fig 2



- | | | |
|-------------|----------------------------|---------------|
| 1 : 絶縁性基板 | 6 : n ⁺ -a-Si 膜 | 11 : 層間絶縁膜 |
| 2 : ゲート電極配線 | 7 : ソース電極配線 | 12 : コンタクトホール |
| 2a : ゲート電極 | 7a : ソース電極 | 13 : 反射画素電極 |
| 3 : 共通電極配線 | 8 : ドレイン電極 | |
| 4 : ゲート絶縁膜 | 9 : チャンネル部 | |
| 5 : a-Si 膜 | 10 : パッシベーション膜 | |

Fig 3

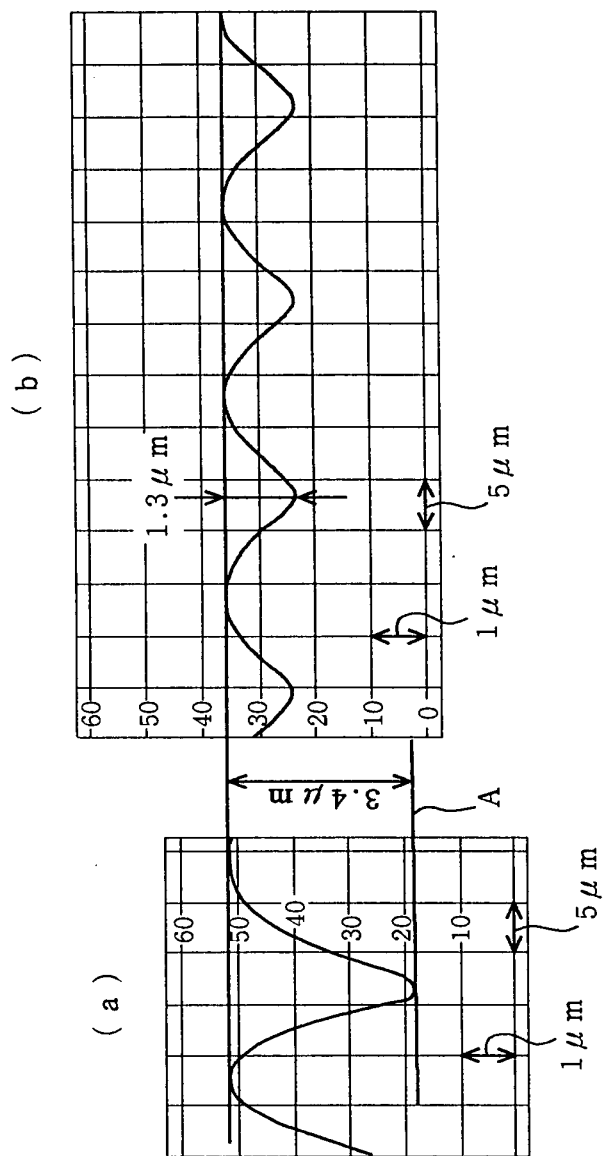


Fig 4

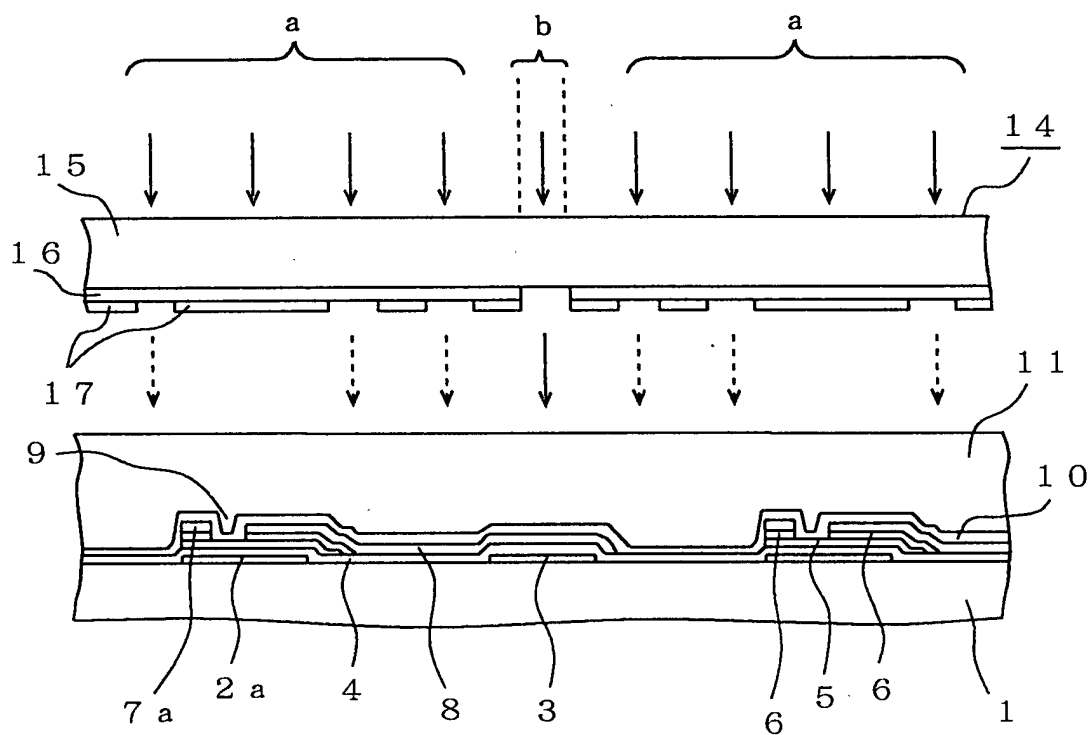


Fig 5

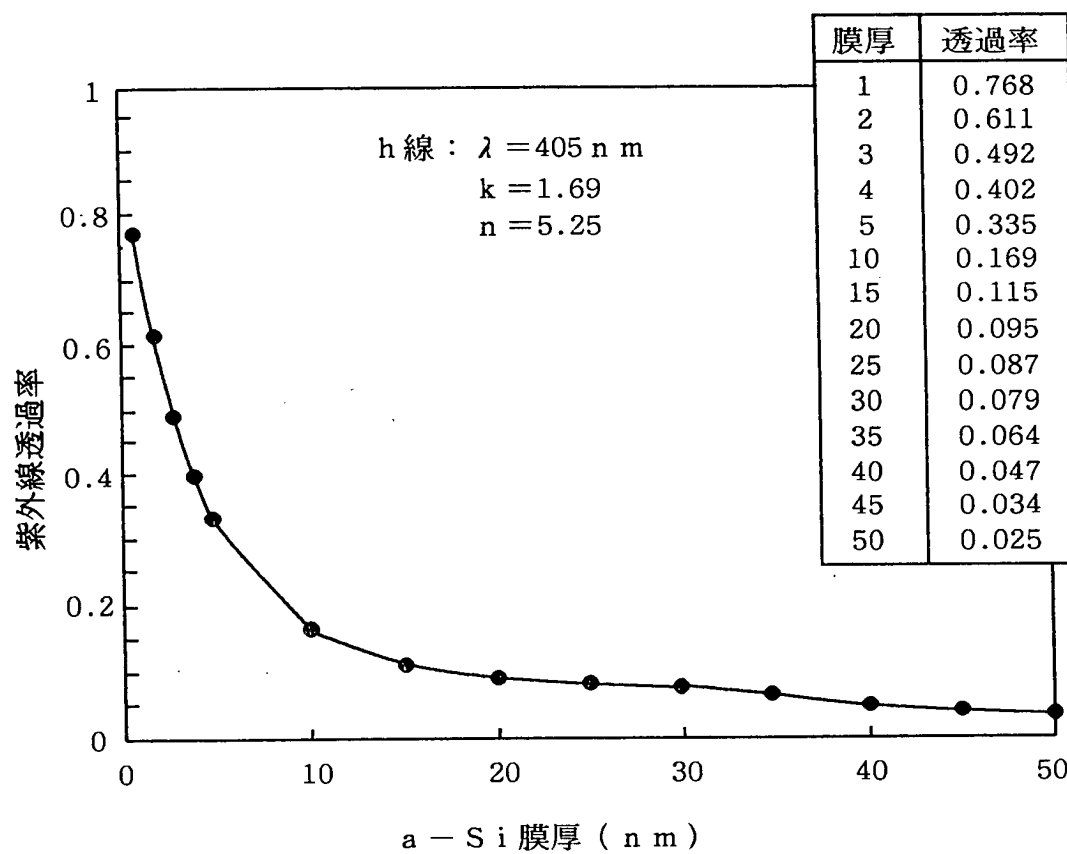


Fig 6

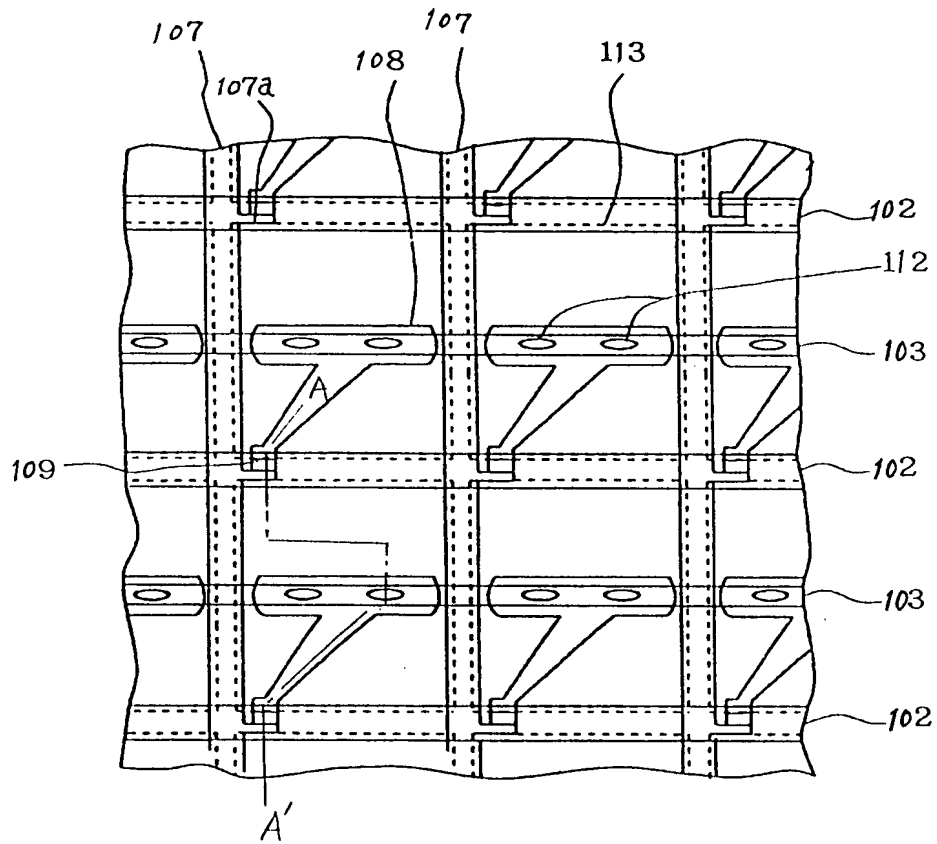
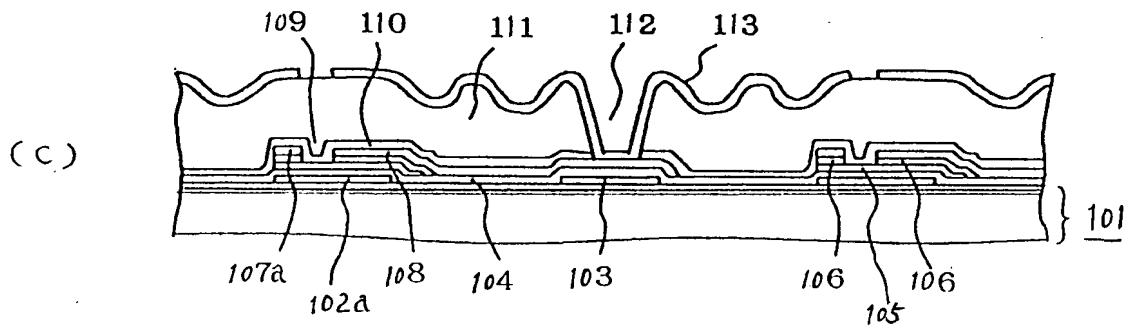
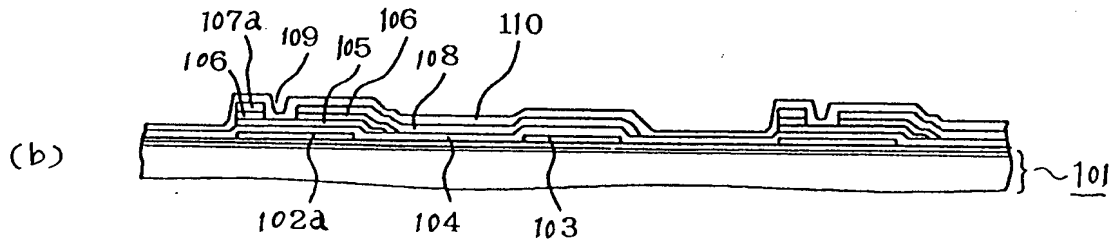
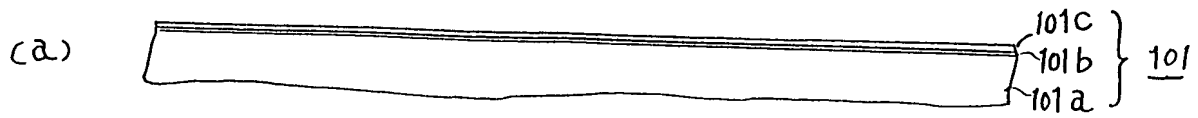
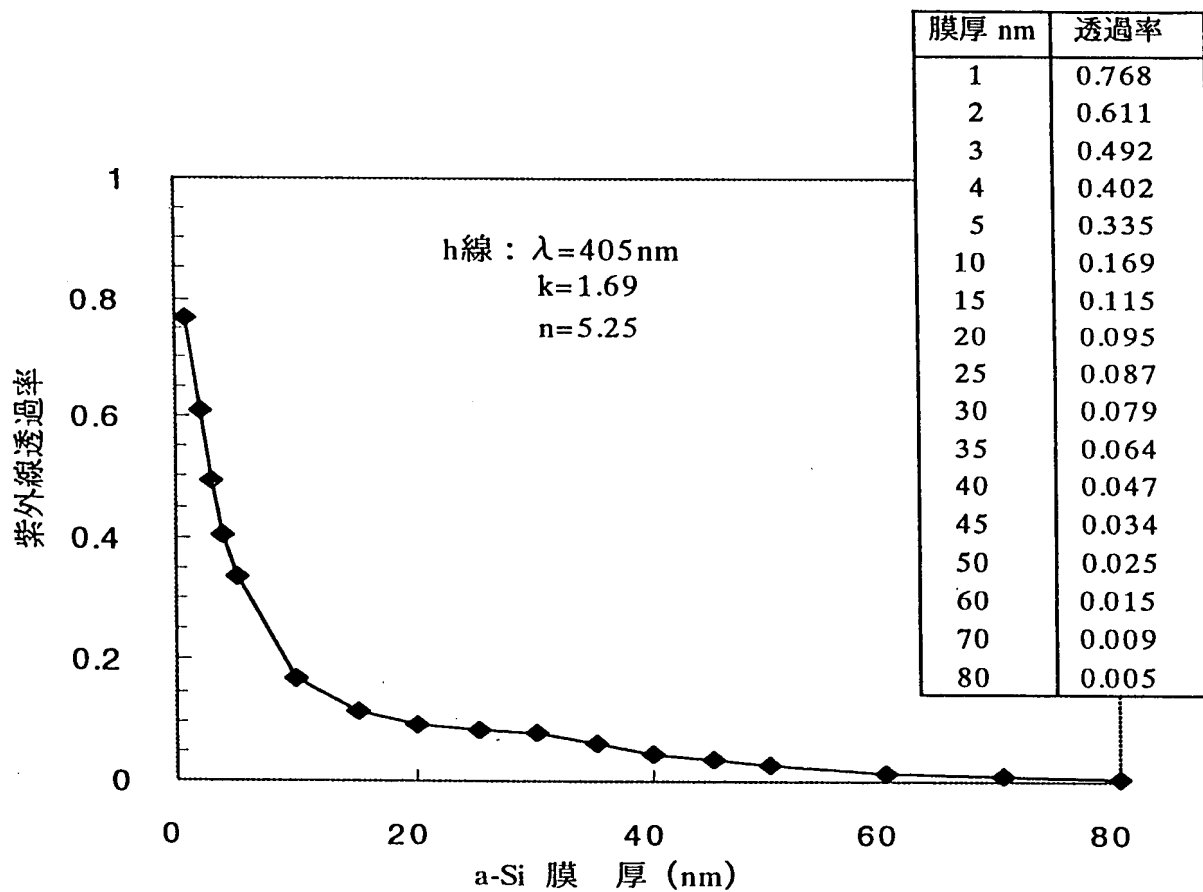


Fig 7



This figure is a schematic diagram of a substrate with a complex top layer structure. The substrate is labeled 101. The top layer is divided into several regions, each labeled with a number. The regions are labeled 107a, 109, 106, 105, 108, 110, 102a, 104, and 103. The regions 107a, 109, 106, 105, 108, 110, 102a, 104, and 103 are shown in cross-section. The regions 107a, 109, 106, 105, 108, 110, 102a, 104, and 103 are shown in cross-section. The regions 107a, 109, 106, 105, 108, 110, 102a, 104, and 103 are shown in cross-section.

Fig 8



a-Si 膜厚に対する紫外線透過率 (計算値)

Fig 9

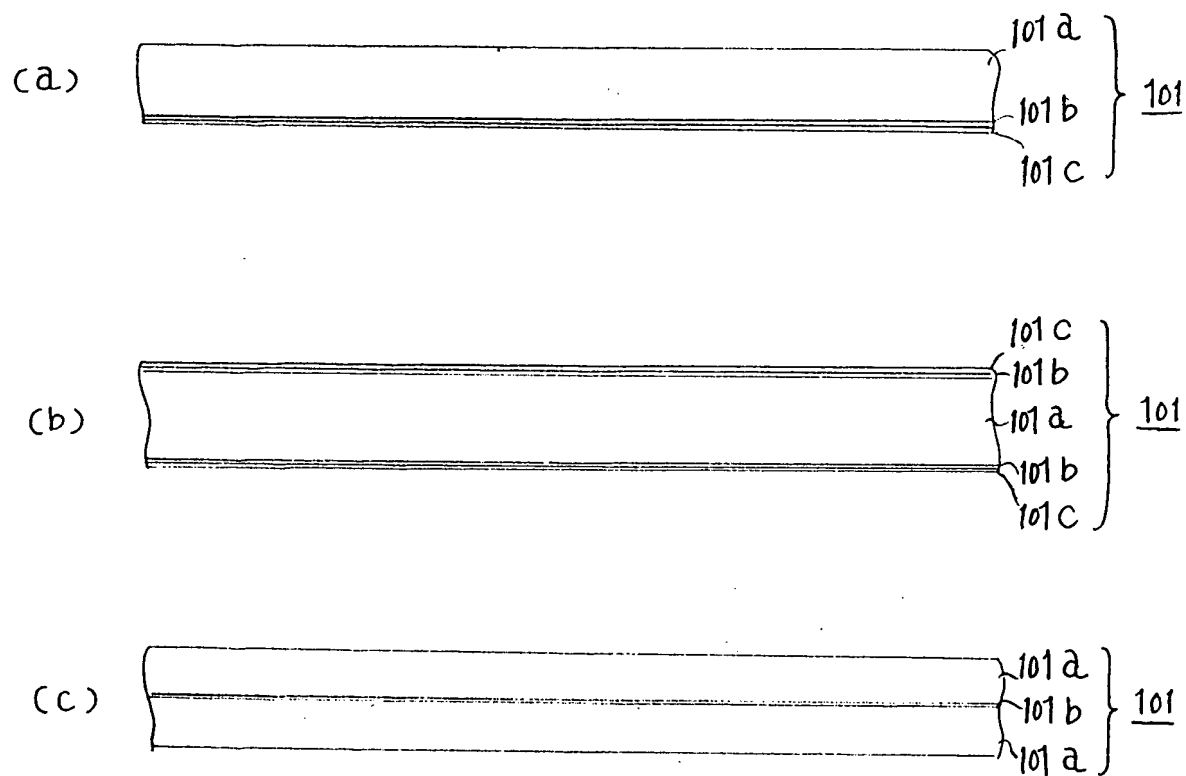


Fig 10

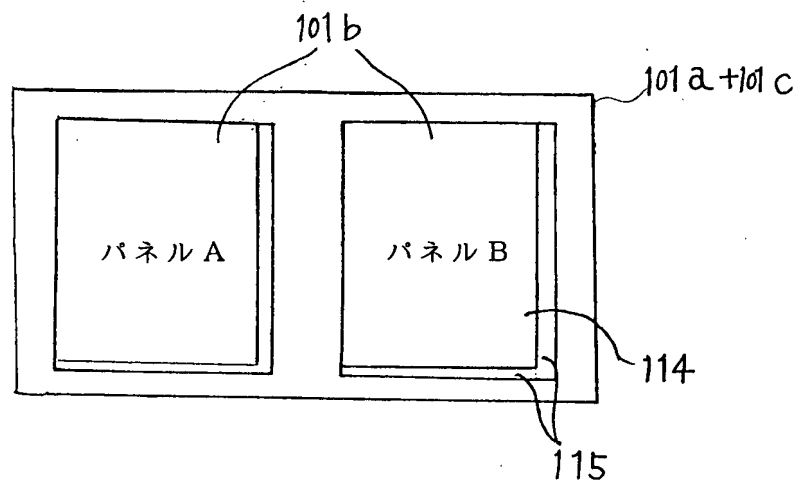


Fig 11

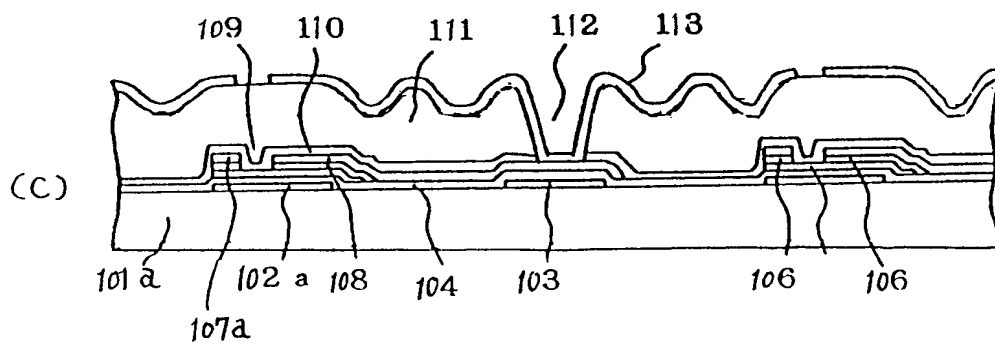
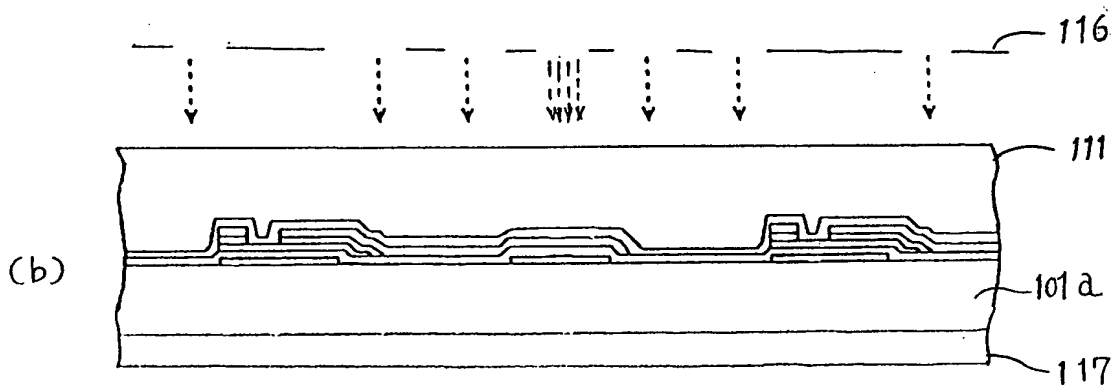
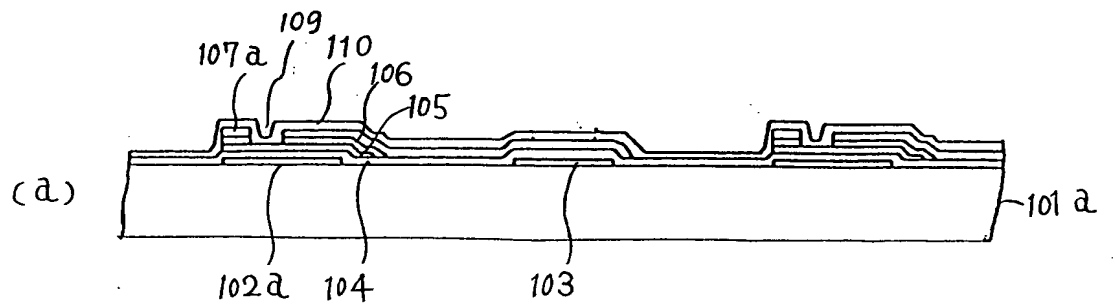


Fig 12

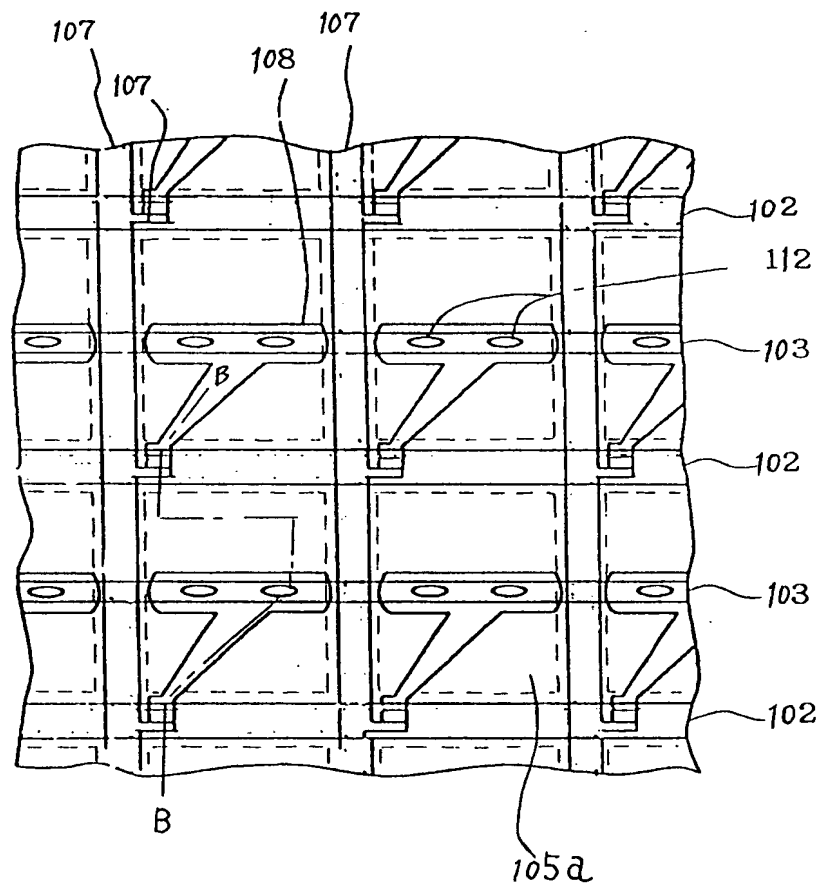


Fig 13

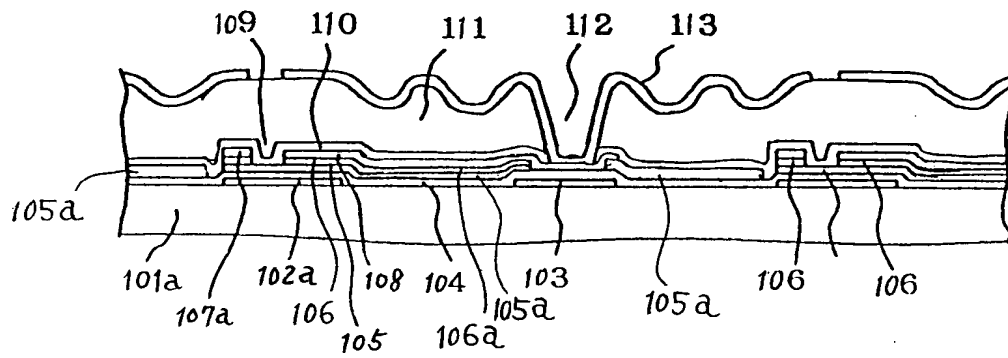


Fig 14

